

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions,  
and listings, of claims in the application:

LISTING OF CLAIMS:

1. (original) A semiconductor device, comprising:  
bonding pads that are formed on a semiconductor substrate;  
an upper copper layer that is formed on the lower surface of said  
bonding pads with a barrier metal interposed; and  
a lower copper layer that is formed closer to said semiconductor  
substrate than said upper copper layer;  
wherein a copper area of said lower copper layer under said  
bonding pads is equal to or lower than that of said upper copper  
layer.
2. (original) A semiconductor device according to claim 1,  
wherein said lower copper layer is electrically insulated from  
said upper copper layer.
3. (original) A semiconductor device according to claim 1,  
wherein the copper area ratio of said upper copper layer is  
greater than that of other copper layers that are formed as  
circuit interconnects on said semiconductor substrate.
4. (original) A semiconductor device according to claim 1,  
wherein the copper area ratio of said upper copper layer is at  
least 70%.

5. (original) A semiconductor device according to claim 1, wherein the planar dimensions of said bonding pads and said upper copper layer are substantially equal.

6. (original) A semiconductor device according to claim 1, wherein said upper copper layer is constituted by a plurality of copper layers.

7. (original) A semiconductor device according to claim 6, wherein the copper area ratios of each copper layer of said upper copper layer are substantially the same.

8. (original) A semiconductor device according to claim 6, further comprising:  
interlevel dielectric films that are provided between each of the copper layers of said upper copper layer; and via-plugs composed of copper that are embedded in said interlevel dielectric films;  
wherein each of the copper layers of said upper copper layer are connected by way of said via-plugs.

9. (original) A semiconductor device according to claim 8, wherein the copper layer pattern of the copper layer that is positioned uppermost in said upper copper layer and said via-plugs that are connected to the copper layer pattern are embedded in a dielectric film that is composed of a first material.

10. (original) A semiconductor device according to claim 1, wherein the copper area ratio of said lower copper layer is at least 15% and not greater than 95%.

11. (original) A semiconductor device according to claim 1, wherein said lower copper layer is constituted by a plurality of copper layers.

12-13. (canceled)

14. (original) A semiconductor device according to claim 13, wherein each of the copper layers of said lower copper layer are constituted by a copper pattern that is embedded in a dielectric film that is composed of a second material having a lower relative dielectric constant than said first material.

15-41. (canceled)

42. (new) A semiconductor device comprising:  
a bonding region in which a bonding pad is formed;  
an internal circuit region provided inside of said bonding region, said internal circuit region having a multilevel wiring structure that includes a plurality of copper interconnect layers at a first level and a plurality of copper interconnect layers at second level; and  
a copper layer formed in said bonding region under said bonding pad in electrical contact therewith, one of said copper interconnect layers at said first level being elongated from said

internal circuit region to said bonding region under said copper layer in electrical isolation therefrom.

43. (new) The device as claimed in claim 42, wherein one of said copper interconnect layers at said second level is further elongated from said internal circuit region to said bonding region under said copper layer in electrical isolation from said copper layer and from one of said copper interconnect layers at said first level.

44. (new) The device as claimed in claim 42, wherein said copper layer includes first and second copper layers and a via-plug sandwiched therebetween.

45. (new) The device as claimed in claim 44, wherein said multilevel wiring structure further includes a plurality of copper interconnect layers at a third level and a plurality of copper interconnect layers at a fourth level, said first copper layer being formed at said third level and said second copper layer being formed at said fourth level.

46. (new) The device as claimed in claim 45, wherein said bonding pad is in electrical contact with said second copper layer, and one of said copper interconnect layers at said fourth level has an electrical contact with said second copper layer.

47. (new) The device as claimed in claim 43, wherein said copper layer includes first and second copper layers and a via-plug sandwiched therebetween, and said bonding pad is in electrical contact with said second copper layer.

48. (new) The device as claimed in claim 47, wherein said multilevel wiring structure further includes a plurality of copper interconnect layers at a third level and a plurality of copper interconnect layers at a fourth level, said first copper layer being formed at said third level and said second copper layer being formed at said fourth level.

49. (new) The device as claimed in claim 48, wherein said bonding pad is in electrical contact with said second copper layer via a barrier metal layer and one of said copper interconnect layers at said fourth level has an electrical contact with said second copper layer.